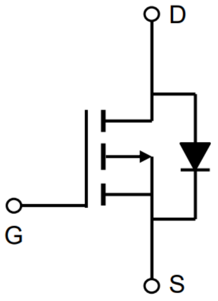
WLP50P06T

-60V P-Channel Enhancement Mode MOSFET

Description



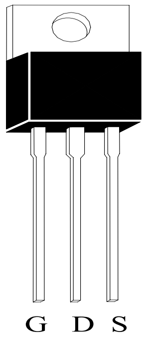
The WLP50P06 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = -60V I_D =-80A

$R_{DS(ON)}$ < -18mΩ @ V_{GS}=-10V

TO-220



Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
WLP50P06	TO-220-3L	WLP50P06 XXYYYY	1000
WLE50P06	TO-263-3L	WLP50P06 XXYYYY	1000

Absolute Maximum Ratings (TC=25℃ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current[1]	-80	A
I_D@T_C=100˚C	Continuous Drain Current[1]	-34	A
I_{DM}	Pulsed Drain Current[2]	-90	A
EAS	Single Pulse Avalanche Energy[3]	101	mJ
I_{AS}	Avalanche Current	-45	A
P_D@T_C=25˚C	Total Power Dissipation[4]	86.8	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C
$R_{θJA}$	Thermal Resistance Junction-Ambient [1]	62	˚C/W
$R_{θJC}$	Thermal Resistance Junction-Case[1]	1.44	˚C/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-18A	---	13	18	mΩ
		V_{GS}=-4.5V , I_D=-12A	---	29	35	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	1.8	-3.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-48V , V_{GS}=0V , T_J=25˚C	---	---	1	uA
		V_{DS}=-48V , V_{GS}=0V , T_J=55˚C	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-18A	---	23	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	7	14	
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-12A	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	6.7	---	
Q_{gd}	Gate-Drain Charge		---	5.5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3 , I_D=-1A	---	38	---	ns
T_r	Rise Time		---	23.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	100	---	
T_f	Fall Time		---	6.8	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	3635	---	pF
C_{oss}	Output Capacitance		---	224	---	
C_{rss}	Reverse Transfer Capacitance		---	141	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-20	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25˚C	---	---	-1	V

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

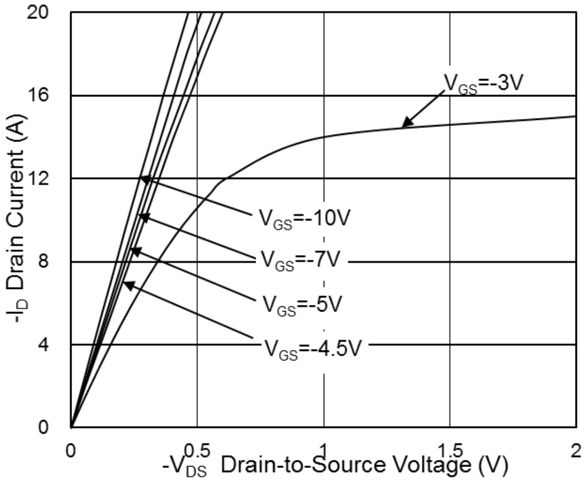
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-45A

4.The power dissipation is limited by 150˚C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics



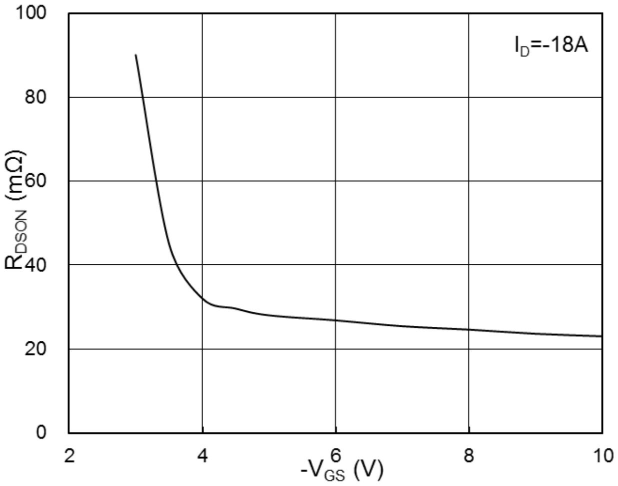
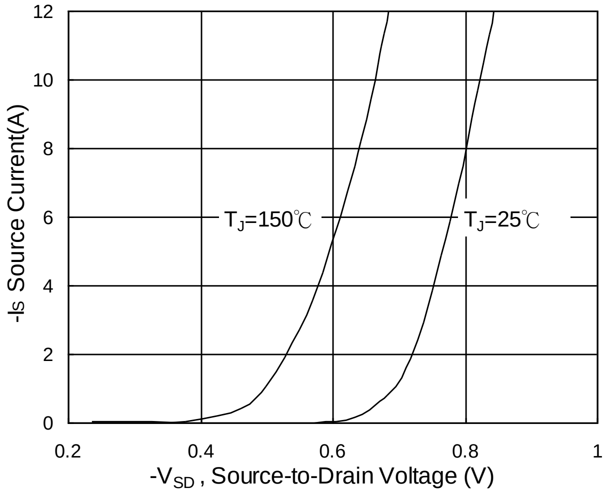


Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs. G-S Voltage



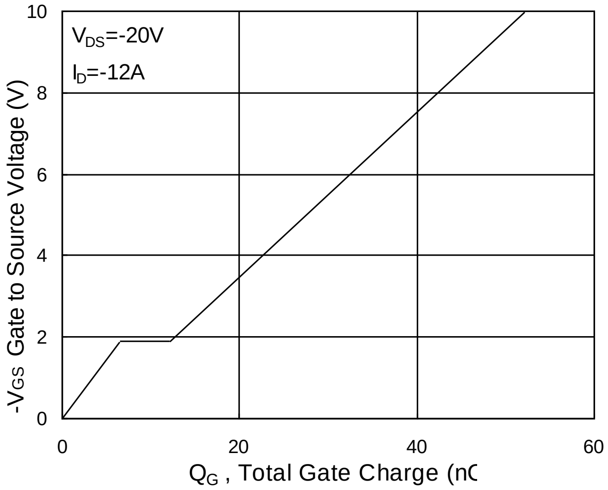
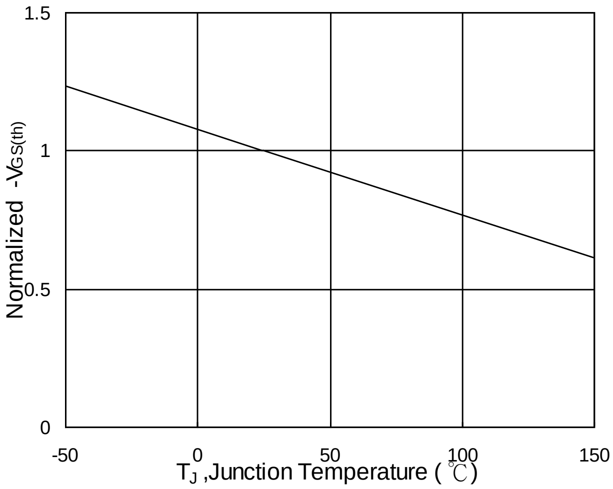


Fig.3 Source Drain Forward Characteristics

Fig.4 Gate-Charge Characteristics



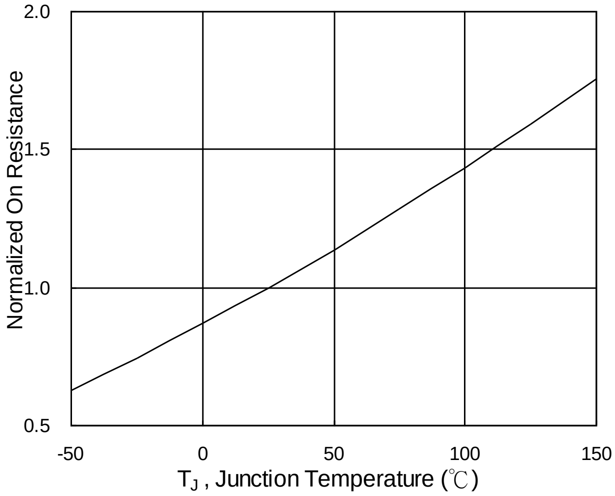


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.6 Normalized R_{DSON} vs. T_J

-60V P-Channel Enhancement Mode MOSFET

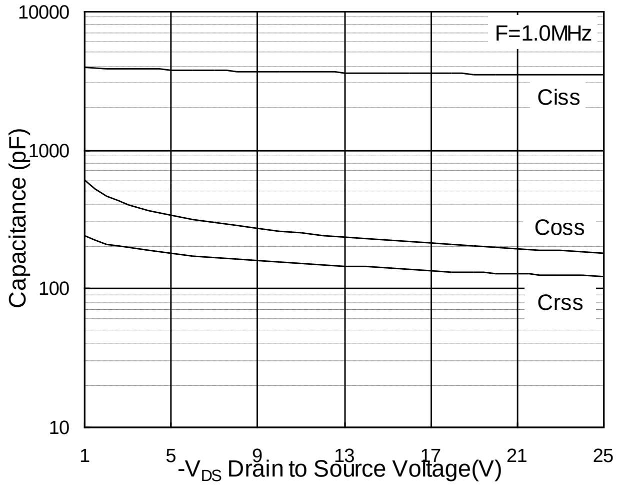


Fig.7 Capacitance

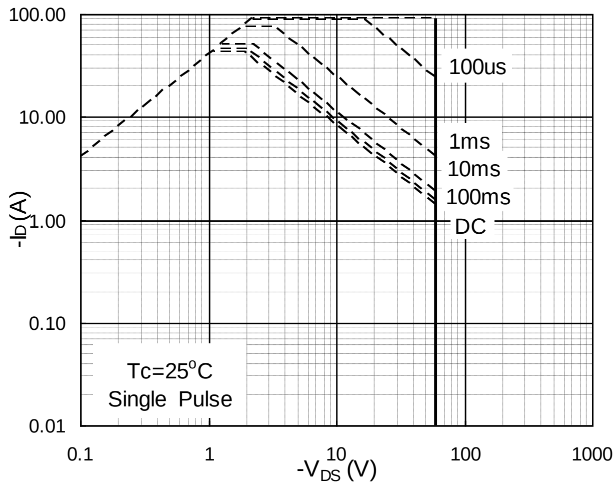


Fig.8 Safe Operating Area

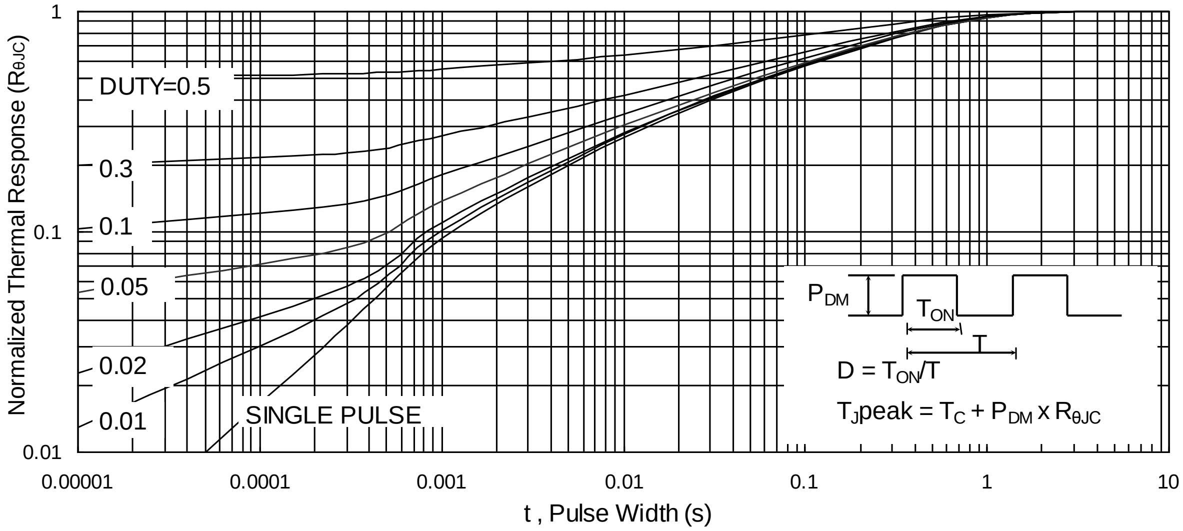


Fig.9 Normalized Maximum Transient Thermal Impedance

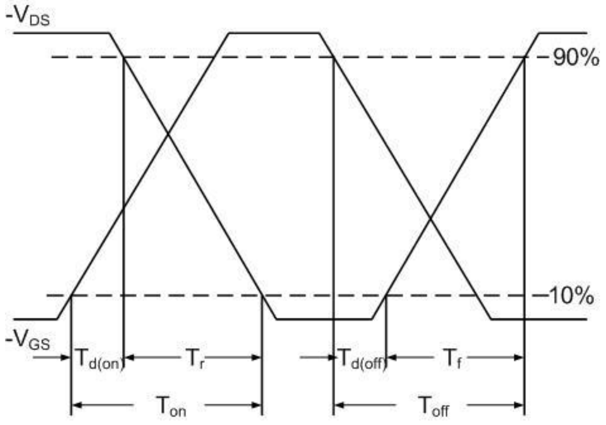


Fig.10 Switching Time Waveform

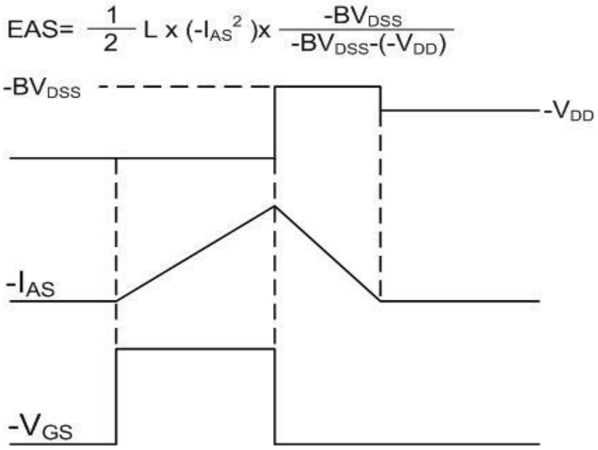
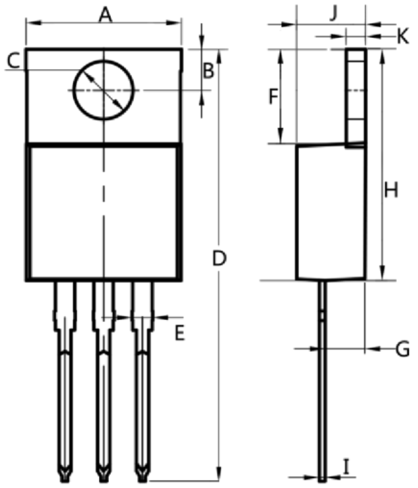


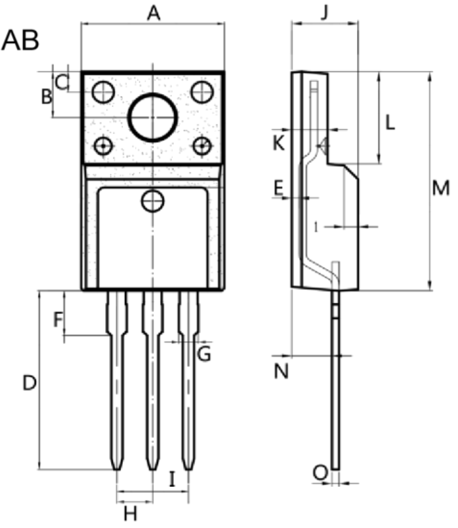
Fig.11 Unclamped Inductive Waveform

TO-220AB



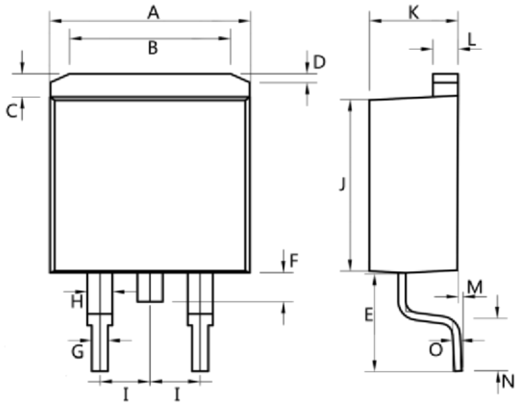
Dim.	Min.	Max.
A	10.0	10.4
B	2.5	3.0
C	3.5	4.0
D	28.0	30.0
E	1.1	1.5
F	6.2	6.6
G	2.9	3.3
H	15.0	16.0
I	0.35	0.45
J	4.3	4.7
K	1.2	1.4
All Dimensions in millimeter		

ITO-220AB



Dim.	Min.	Max.
A	9.9	10.3
B	2.9	3.5
C	1.15	1.45
D	12.75	13.25
E	0.55	0.75
F	3.1	3.5
G	1.25	1.45
H	Typ	2.54
I	Typ	5.08
J	4.55	4.75
K	2.4	2. 7
L	6.35	6.75
M	15.0	16.0
N	2.75	3.15
O	0.45	0.60
All Dimensions in millimeter		

TO-263



Dim.	Min.	Max.
A	10.0	10. 5
B	7.25	7.75
C	1.3	1.5
D	0.55	0.75
E	5.0	6.0
F	1.4	1.6
G	0.75	0.95
H	1.15	1.35
I	Typ	2.54
J	8.4	8.6
K	4.4	4.6
L	1.25	1.45
M	0.02	0.1
N	2.4	2.8
O	0.35	0.45
All Dimensions in millimeter		